

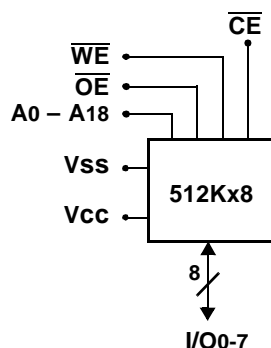
ACT-PS512K8 High Speed 4 Megabit Plastic Monolithic SRAM

Plastic Path™ Features

- Low Power Monolithic CMOS 512K x 8 SRAM
- Operating Temperature Range
 - Full Military (-55°C to +125°C)
 - Industrial (-40°C to +85°C)
- Burn-in and Temperature Cycle Available
- 10, 12, 15, 17, 20 & 25ns Access Times
- +5V Power Supply
- Industry Standard Pinouts
 - Center Power / Ground Pins
- TTL Compatible I/O
- 3.3V Device I/O Interfacing
- JEDEC Standard 36 pin Plastic SOJ Package
 - 36 Lead, .93" x .405" x 0.148 Small Outline J lead (SOJ), Aeroflex code# "L2"
- Fully Static Operation
 - No Clocks or Refresh Required



Block Diagram – SOJ (L2)



Pin Description

I/O0-7	Data I/O
A0-18	Address Inputs
\overline{WE}	Write Enable
\overline{CE}	Chip Enable
\overline{OE}	Output Enable
Vcc	Power Supply
Vss	Ground
NC	Not Connected

General Description

The ACT-PS512K8 is a Plastic High Speed, 4 Megabit (4,194,304 bits) CMOS Monolithic SRAM organized as 524,288 words by 8 bits. Designed for high-speed, high density, high reliability, mass memory and fast cache system applications.

The plastic monolithic is input and output TTL compatible. Writing is executed when the write enable (\overline{WE}) and chip enable (\overline{CE}) inputs are low. Reading is accomplished when \overline{WE} is high and \overline{CE} and output enable (\overline{OE}) are both low. Access time grades of 10ns 12ns, 15ns, 17ns, 20ns and 25ns are standard.

Absolute Maximum Ratings

Symbol	Parameter	MINIMUM	MAXIMUM	Units
T_C	Case Operating Temperature	-55	+125	°C
T_{STG}	Storage Temperature	-65	+150	°C
P_D	Maximum Package Power Dissipation		1.0	W
V_G	Maximum Signal Voltage to Ground	-0.5	$V_{CC} + 0.5$	V
V_{CC}	Power Supply Voltage	-0.5	+7.0	V

Recommended Operating Conditions

Symbol	Parameter	Minimum	Maximum	Units
V_{CC}	Power Supply Voltage	+4.5	+5.5	V
V_{SS}	Ground	0	0	V
V_{IH}	Input High Voltage	+2.2	$V_{CC} + 0.5$	V
V_{IL}	Input Low Voltage	-0.5	+0.8	V
T_C	Operating Temperature (Military)	-55	+125	°C
T_C	Operating Temperature (Industrial)	-40	+85	°C

Truth Table

Mode	\overline{CE}	\overline{WE}	\overline{OE}	Data I/O	Supply Current
Standby	H	X	X	High Z	I_{SB}
Output Disable	L	H	H	High Z	I_{CC}
Read	L	H	L	Data OUT	I_{CC}
Write	L	L	X	Data IN	I_{CC}

Capacitance

(V_{IN} & $V_{OUT} = 0V$, $f = 1MHz$, $T_C = 25^\circ C$, unless otherwise noted, Guaranteed but not tested)

Symbol	Parameter	Maximum	Units
C_{IN}	Input Capacitance (A_{0-18} , \overline{WE} & \overline{OE})	6	pF
C_{OUT}	Output Capacitance (I/O_{0-7} & \overline{CE})	8	pF

DC Characteristics

($V_{CC} = 5.0V$, $V_{SS} = 0V$, $T_C = -55^\circ C$ to $+125^\circ C$ or $-40^\circ C$ to $+85^\circ C$)

Parameter	Sym	Conditions	Min	Max	Units
Input Leakage Current	I_{LI}	$V_{CC} = \text{Max}$, $V_{IN} = V_{SS}$ to V_{CC}	-10	+10	μA
Output Leakage Current	I_{LO}	$\overline{CE} = V_{IH}$, $\overline{OE} = V_{IH}$, $V_{OUT} = V_{SS}$ to V_{CC}	-10	+10	μA
Operating Supply Current	I_{CC}	$\overline{CE} = V_{IL}$, $\overline{OE} = V_{IH}$, $f = 5MHz$, $V_{CC} = 5.5V$		130	mA
Standby Current	I_{SB}	$\overline{CE} = V_{IH}$, $\overline{OE} = V_{IH}$, $f = 5MHz$, $V_{CC} = 5.5V$		20	mA
Output Low Voltage	V_{OL}	$I_{OL} = 8 \text{ mA}$, $V_{CC} = 4.5V$		0.4	V
Output High Voltage	V_{OH}	$I_{OH} = -4 \text{ mA}$, $V_{CC} = 4.5V$	2.4		V

Note: DC Test conditions: $V_{IL} = 0.3V$, $V_{IH} = V_{CC} - 0.3V$.

AC Characteristics

(V_{CC} = 5.0V, V_{SS} = 0V, T_C = -55°C to +125°C or -40°C to +85°C)

Read Cycle

Parameter	Sym	-010		-012		-015		-017		-020		-025		Units
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t _{RC}	10		12		15		17		20		25		ns
Address Access Time	t _{AA}		10		12		15		17		20		25	ns
Chip Enable Access Time	t _{ACE}		10		12		15		17		20		25	ns
Output Hold from Address Change	t _{OH}	3		3		3		3		4		5		ns
Output Enable to Output Valid	t _{OE}		5		6		7		8		10		12	ns
Chip Enable to Output in Low Z (1)	t _{CLZ}	3		3		3		3		3		3		ns
Output Enable to Output in Low Z (1)	t _{OLZ}	0		0		0		0		0		0		ns
Chip Deselect to Output in High Z (1)	t _{CHZ}		5		6		7		7		8		10	ns
Output Disable to Output in High Z (1)	t _{OHZ}		5		6		7		7		8		10	ns

Note 1. Guaranteed by design, but not tested

Write Cycle

Parameter	Sym	-010		-012		-015		-017		-020		-025		Units
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{WC}	10		12		15		17		20		25		ns
Chip Enable to End of Write	t _{CW}	7		8		10		12		13		15		ns
Address Valid to End of Write	t _{AW}	7		8		10		12		13		15		ns
Data Valid to End of Write	t _{DW}	5		6		8		8		9		10		ns
Write Pulse Width	t _{WP}	7		8		10		12		13		15		ns
Address Setup Time	t _{AS}	0		0		0		0		0		0		ns
Address Hold Time	t _{AH}	0		0		0		0		0		0		ns
Output Active from End of Write (1)	t _{OW}	3		3		3		3		4		5		ns
Write to Output in High Z (1)	t _{WHZ}		5		6		7		8		8		10	ns
Data Hold from Write Time	t _{DH}	0		0		0		0		0		0		ns

Note 1. Guaranteed by design, but not tested

Data Retention Electrical Characteristics (Special Order Only)

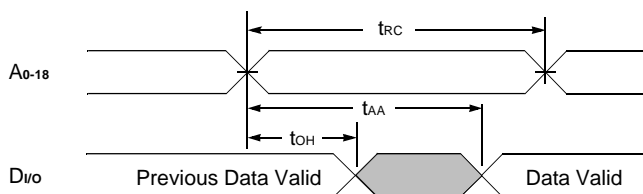
V_{CC} = 5.0V, V_{SS} = 0V, T_C = -55°C to +125°C or -40°C to +85°C)

Parameter	Sym	Test Conditions	All Speeds			Units
			Min	Typ	Max	
V _{CC} for Data Retention	V _{DR}	$\overline{CE} \geq V_{CC} - 0.2V$	2		5.5	V
Data Retention Current	I _{CCDR1}	V _{CC} = 3V		0.5	2.0	mA

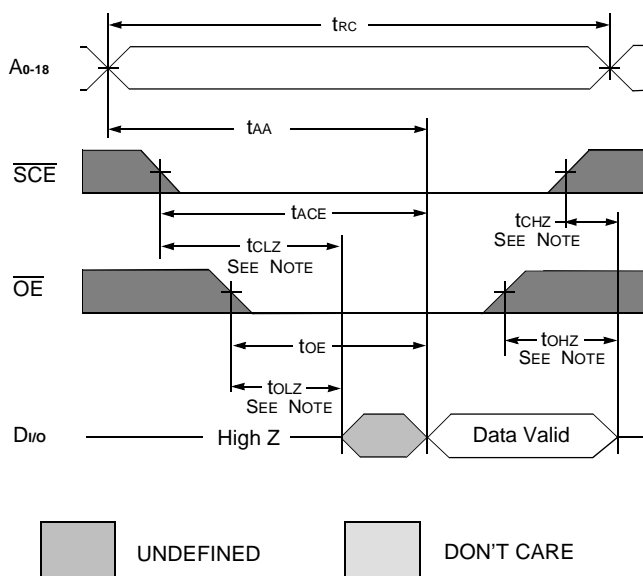
Timing Diagrams — SRAM

Read Cycle Timing Diagrams

Read Cycle 1 ($\overline{\text{SCE}} = \overline{\text{OE}} = \text{V}_{\text{IL}}$, $\overline{\text{SWE}} = \text{V}_{\text{IH}}$)

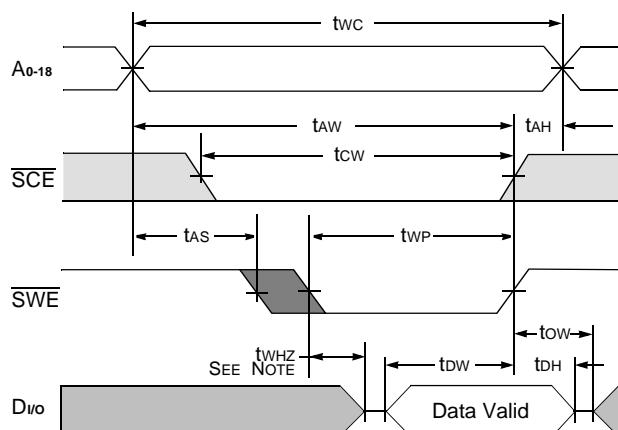


Read Cycle 2 ($\overline{\text{SWE}} = \text{V}_{\text{IH}}$)

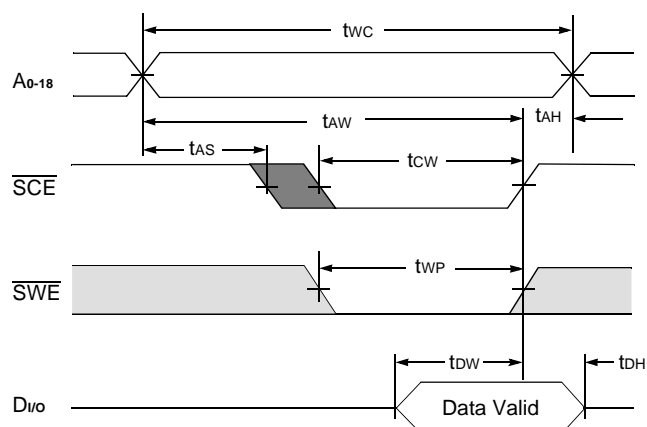


Write Cycle Timing Diagrams

Write Cycle ($\overline{\text{SWE}}$ Controlled, $\overline{\text{OE}} = \text{V}_{\text{IH}}$)

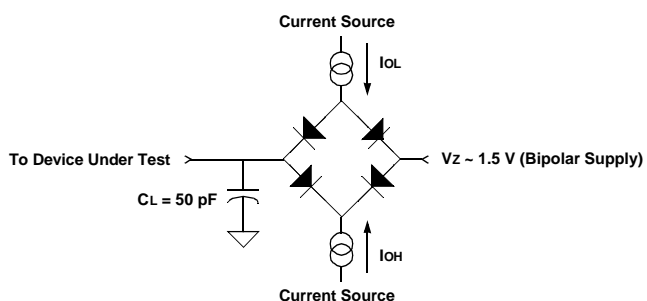


Write Cycle ($\overline{\text{SCE}}$ Controlled, $\overline{\text{OE}} = \text{V}_{\text{IH}}$)



Note: Guaranteed by design, but not tested.

AC Test Circuit



AC Test Conditions

Parameter	Typical	Units
Input Pulse Level	0 – 3.0	V
Input Rise and Fall	5	ns
Input and Output Timing Reference Level	1.5	V

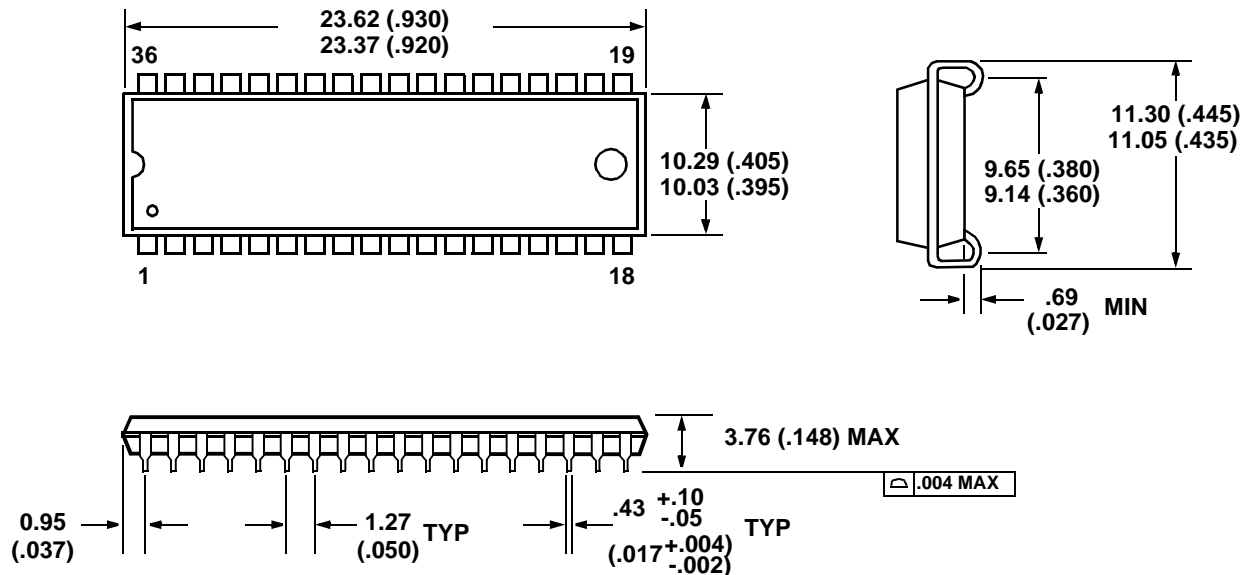
Notes:

1) VZ is programmable from -2V to +7V. 2) IOL and IOH programmable from 0 to 16 mA. 3) Tester Impedance $Z_o = 75\Omega$. 4) VZ is typically the midpoint of V_{OH} and V_{OL} . 5) IOL and IOH are adjusted to simulate a typical resistance load circuit. 6) ATE Tester includes jig capacitance.

Pin Numbers & Functions

36 Pins — SOJ			
Pin #	Function	Pin #	Function
1	A ₀	19	NC
2	A ₁	20	A ₁₀
3	A ₂	21	A ₁₁
4	A ₃	22	A ₁₂
5	A ₄	23	A ₁₃
6	\overline{CE}	24	A ₁₄
7	I/O ₀	25	I/O ₄
8	I/O ₁	26	I/O ₅
9	V _{CC}	27	V _{CC}
10	V _{SS}	28	V _{SS}
11	I/O ₂	29	I/O ₆
12	I/O ₃	30	I/O ₇
13	\overline{WE}	31	\overline{OE}
14	A ₅	32	A ₁₅
15	A ₆	33	A ₁₆
16	A ₇	34	A ₁₇
17	A ₈	35	A ₁₈
18	A ₉	36	NC

Package Outline "L2" — SOJ Package, 36 Leads



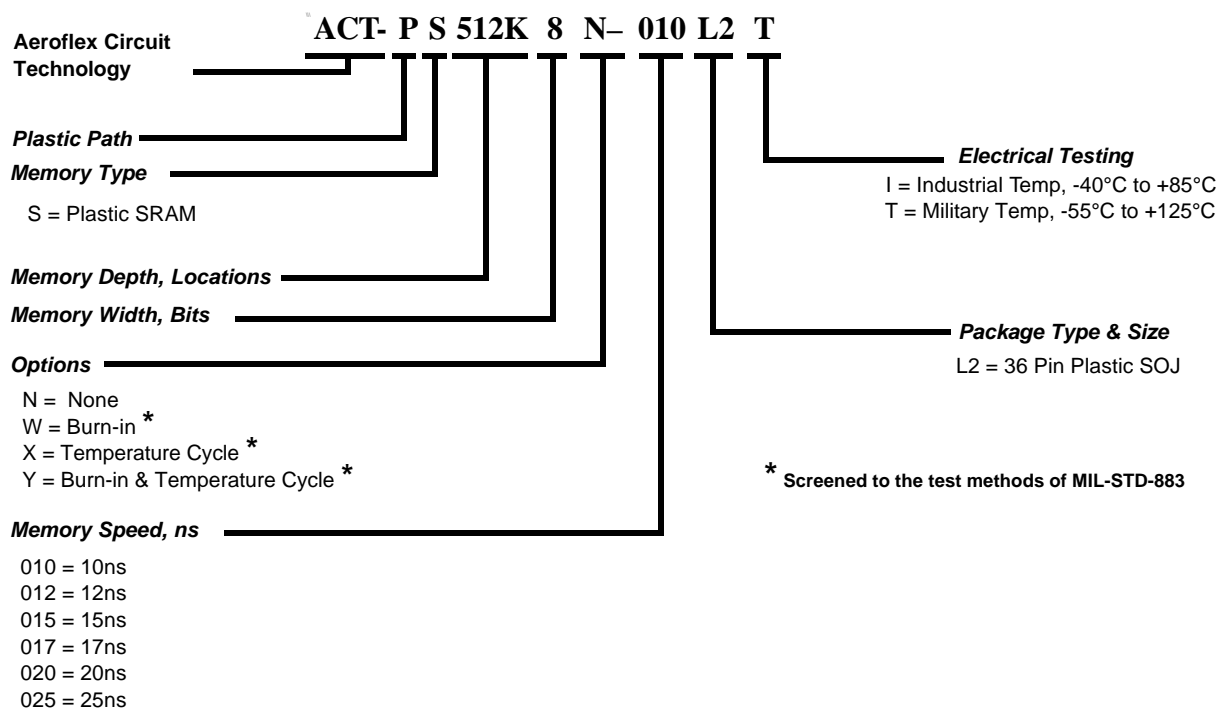
All dimensions in inches
 Dimensions in millimeters mm
 Dimensions in inches (.xxx)



Ordering Information (Typical)

Model Number	Options	Speed	Package
ACT-PS512K8N-010L2I	None	10ns	36 Lead SOJ
ACT-PS512K8W-012L2I	Burn-in	12ns	36 Lead SOJ
ACT-PS512K8X-015L2T	Temp Cycle	15ns	36 Lead SOJ
ACT-PS512K8Y-017L2T	Temp Cycle & Burn-in	17ns	36 Lead SOJ
ACT-PS512K8Y-020L2T	Temp Cycle & Burn-in	20ns	36 Lead SOJ
ACT-PS512K8Y-025L2T	Temp Cycle & Burn-in	25ns	36 Lead SOJ

Part Number Breakdown



Aeroflex Circuit Technology
35 South Service Road
Plainview New York 11830

Telephone: (516) 694-6700
FAX: (516) 694-6715
Toll Free Inquiries: 1-(800) 843-1553